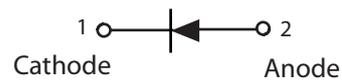
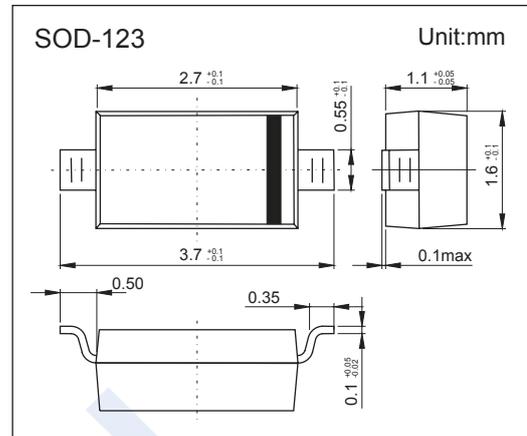


Switching Diodes

L1N4148WT1G

■ Features

- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance
- Surface Mount Package Ideally Suited for Automatic Insertion
- Pb-Free package is available

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V	
Peak Repetitive Reverse Voltage	V_{RRM}	75		
Working Peak Reverse Voltage	V_{RWM}			
DC Blocking Voltage	V_R			
RMS Reverse Voltage	$V_{R(RMS)}$	53		
Average Rectified Output Current	I_o	200	mA	
Repetitive Rectified Output Current	I_{FM}	300		
Non-Repetitive Peak Forward Surge Current	I_{FSM}	$t=1\mu\text{s}$	2	A
		$t=1\text{s}$	1	
Power Dissipation	P_D	425	mW	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	290	$^\circ\text{C}/\text{W}$	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature range	T_{stg}	-65 to 150		

Switching Diodes

L1N4148WT1G

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100\ \mu\text{A}$	100			V
Forward voltage	V_F	$I_F = 1\ \text{mA}$			0.715	
		$I_F = 10\ \text{mA}$			0.855	
		$I_F = 50\ \text{mA}$			1	
		$I_F = 150\ \text{mA}$			1.25	
Reverse voltage leakage current	I_R	$V_R = 75\ \text{V}$			2.5	μA
		$V_R = 75\ \text{V}, T_J = 150^\circ\text{C}$			50	
		$V_R = 20\ \text{V}$			25	nA
		$V_R = 25\ \text{V}, T_J = 25^\circ\text{C}$			30	μA
Capacitance between terminals	C_T	$V_R = 0\ \text{V}, f = 1\ \text{MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\ \text{mA}, I_{rr} = 0.1 \times I_R, R_L = 100\ \Omega$			4	ns

■ Marking

Marking	T4
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■ Typical Characteristics

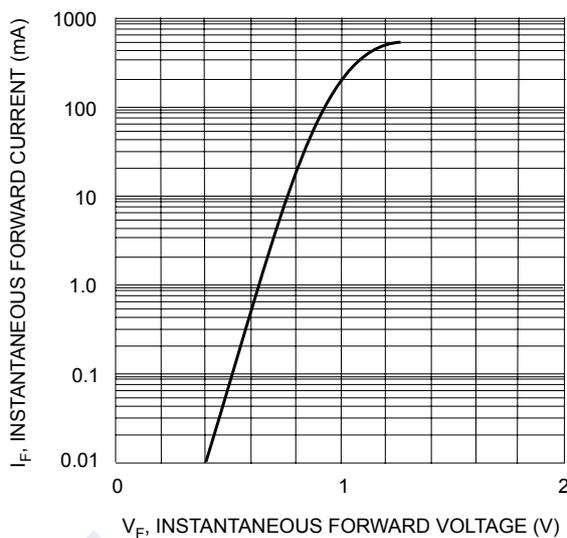


Fig. 1 Forward Characteristics

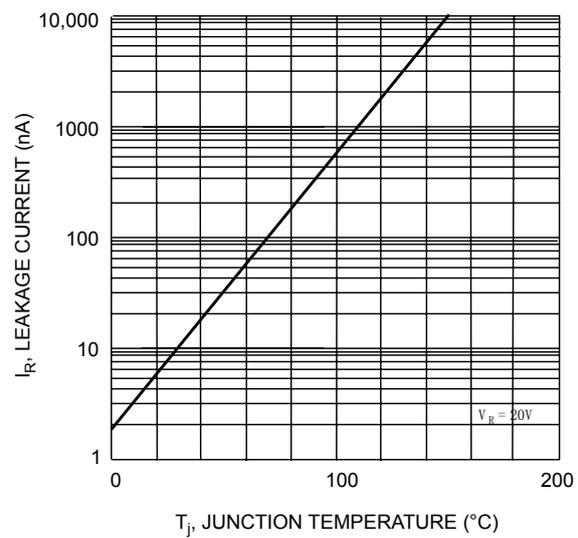


Fig. 2 Leakage Current vs Junction Temperature